

Type Number	Data Sheet	Description	Features and benefits	Target applications	Status
PESD5V0C1BSF	<a href="#">PESD5V0C1BSF.pdf</a>	Ultra low capacitance bidirectional ESD protection diode Ultra low capacitance bidirectional ElectroStatic Discharge (ESD) protection diode, part of the TrEOS Protection family. This device is housed in a DSN0603-2 (SOD962) leadless ultra small Surface-Mounted Device (SMD) package. The TrEOS Protection family is optimized for safeguarding very sensitive high-speed interfaces against ESD pulses with a high level of robustness.	<ul style="list-style-type: none"> <li>• Bidirectional ESD protection of one line</li> <li>• Extremely low diode capacitance <math>C_d = 0.2 \text{ pF}</math></li> <li>• ESD protection up to <math>\pm 20 \text{ kV}</math> according to IEC 61000-4-2</li> <li>• Ultra small SMD package</li> </ul>	<ul style="list-style-type: none"> <li>• ultra high-speed datalines</li> <li>• very sensitive interface lines</li> <li>• generic interface lines</li> </ul>	Production
PESD5V0H1BSF	<a href="#">PESD5V0H1BSF.pdf</a>	Ultra low capacitance bidirectional ESD protection diode Ultra low capacitance bidirectional ElectroStatic Discharge (ESD) protection diode, part of the TrEOS Protection family. This device is housed in a DSN0603-2 (SOD962) leadless ultra small Surface-Mounted Device (SMD) package. The TrEOS Protection family is optimized for safeguarding very sensitive high-speed interfaces against ESD pulses with a high level of robustness.	<ul style="list-style-type: none"> <li>• Bidirectional ESD protection of one line</li> <li>• Extremely low diode capacitance: <ul style="list-style-type: none"> <li>• <math>C_d = 0.15 \text{ pF}</math> at 1 MHz</li> <li>• <math>C_d = 0.13 \text{ pF}</math> at 2.5 GHz</li> </ul> </li> <li>• ESD protection up to <math>\pm 15 \text{ kV}</math> according to IEC 61000-4-2</li> <li>• Ultra small SMD package</li> </ul>	<ul style="list-style-type: none"> <li>• ultra high-speed datalines</li> <li>• very sensitive interface lines</li> <li>• generic interface lines</li> </ul>	Production
PMCM4401VNE	<a href="#">PMCM4401VNE.pdf</a>	12V, N-channel Trench MOSFET N-channel enhancement mode Field-Effect Transistor (FET) in a 4 bumps Wafer Level Chip-Size Package (WLCSP) using Trench MOSFET technology.	<ul style="list-style-type: none"> <li>• Low threshold voltage</li> <li>• Ultra small package: <math>0.78 \times 0.78 \times 0.35 \text{ mm}</math></li> <li>• Trench MOSFET technology</li> <li>• ElectroStatic Discharge (ESD) protection <math>&gt; 2 \text{ kV}</math> HBM</li> </ul>	<ul style="list-style-type: none"> <li>• Relay driver</li> <li>• High-speed line driver</li> <li>• Low-side loadswitch</li> <li>• Switching circuits</li> </ul>	Production
PMCM6501VPE	<a href="#">PMCM6501VPE.pdf</a>	12 V, P-channel Trench MOSFET P-channel enhancement mode Field-Effect Transistor (FET) in a 6 bumps Wafer Level Chip-Size Package (WLCSP) using Trench MOSFET technology.	<ul style="list-style-type: none"> <li>• Low threshold voltage</li> <li>• Ultra small package: <math>0.98 \times 1.48 \times 0.35 \text{ mm}</math></li> <li>• Trench MOSFET technology</li> <li>• ElectroStatic Discharge (ESD) protection <math>&gt; 2 \text{ kV}</math> HBM</li> </ul>	<ul style="list-style-type: none"> <li>• Battery switch</li> <li>• High-speed line driver</li> <li>• Low-side loadswitch</li> <li>• Switching circuits</li> </ul>	Production
PMEG2002AESF	<a href="#">PMEG2002AESF.pdf</a>	20 V, 0.2 A low VF MEGA Schottky barrier rectifier Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection in a DSN0603-2 (SOD962-2) leadless ultra small Surface-Mounted Device (SMD) package.	<ul style="list-style-type: none"> <li>• Average forward current <math>I_F(AV) \leq 0.2 \text{ A}</math></li> <li>• Reverse voltage <math>V_R \leq 20 \text{ V}</math></li> <li>• Low forward voltage typ. <math>V_F = 245 \text{ mV}</math></li> <li>• Low reverse current typ. <math>I_R = 5 \mu\text{A}</math></li> <li>• Ultra small and leadless SMD package</li> <li>• Read more</li> </ul>	<ul style="list-style-type: none"> <li>• Low voltage rectification</li> <li>• High efficiency DC-to-DC conversion</li> <li>• Switch mode power supply applications</li> <li>• Ultra high-speed switching</li> <li>• Read more</li> </ul>	Production

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PMEG45U10EPD	PMEG45U10EPD.pdf	45 V, 10 A extremely low VF MEGA Schottky barrier rectifier Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOT1289 (CFP15) power and flat lead Surface-Mounted Device (SMD) plastic package.	<ul style="list-style-type: none"> <li>Average forward current: <math>IF(AV) \leq 10</math> A</li> <li>Reverse voltage: <math>VR \leq 45</math> V</li> <li>Extremely low forward voltage</li> <li>High power capability due to clip-bonding technology and heat sink</li> <li>Small and thin SMD power plastic package, typical height 0.78 mm</li> </ul>	<ul style="list-style-type: none"> <li>Low voltage rectification</li> <li>High efficiency DC-to-DC conversion</li> <li>Switch mode power supply</li> <li>Freewheeling application</li> <li>Reverse polarity protection</li> <li>Read more</li> </ul>	Production
PMEG6010ER	PMEG6010ER.pdf	1 A low V_F MEGA Schottky barrier rectifier Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD123W small and flat lead Surface-Mounted Device (SMD) plastic package.	<ul style="list-style-type: none"> <li>Average forward current: <math>IF(AV) \leq 1</math> A</li> <li>Reverse voltage: <math>VR \leq 60</math> V</li> <li>Low forward voltage</li> <li>High power capability due to clip-bond technology</li> <li>AEC-Q101 qualified</li> <li>Read more</li> </ul>	<ul style="list-style-type: none"> <li>Low voltage rectification</li> <li>High efficiency DC-to-DC conversion</li> <li>Switch Mode Power Supply (SMPS)</li> <li>Reverse polarity protection</li> <li>Low power consumption applications</li> </ul>	Production
PMV50EPEA	PMV50EPEA.pdf	30 V, P-channel Trench MOSFET P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.	<ul style="list-style-type: none"> <li>Logic level compatible</li> <li>Very fast switching</li> <li>Trench MOSFET technology</li> <li>ElectroStatic Discharge (ESD) protection &gt; 2 kV HBM</li> <li>AEC-Q101 qualified</li> </ul>	<ul style="list-style-type: none"> <li>Relay driver</li> <li>High-speed line driver</li> <li>High-side loadswitch</li> <li>Switching circuits</li> </ul>	Production
PTVS5V0Z1USK	PTVS5V0Z1USK.pdf	Transient voltage suppressor in DSN1608-2 for mobile applications Unidirectional Transient Voltage Suppressor (TVS) in a very small leadless DSN1608-2 (SOD964) package.	<ul style="list-style-type: none"> <li>Rated peak pulse current: <math>IPPM = 80</math> A (8/20 <math>\mu</math>s pulse)</li> <li>Rated peak pulse power: <math>PPPM = 1200</math> W (8/20 <math>\mu</math>s pulse)</li> <li>Dynamic resistance <math>R_{dyn} = 0.06</math> <math>\Omega</math></li> <li>Reverse current: <math>IRM = 0.025</math> <math>\mu</math>A</li> <li>Very low package height: 0.29 mm</li> </ul>	<ul style="list-style-type: none"> <li>Power supply protection</li> <li>Industrial application</li> <li>Power management</li> </ul>	Production